



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

SB1045L

TO-277 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

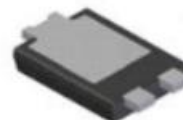
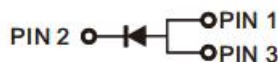
■Features 特点

High surge current capability 高浪涌电流能力

Low forward voltage drop 低正向压降

High reliability 高可靠性

Case 封装:TO-277



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Rating 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	45	V
DC Reverse Voltage 直流反向电压	V_R	45	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	32	V
Forward Rectified Current 正向整流电流	I_F	10	A
Peak Surge Current 峰值浪涌电流	I_{FSM}	180	A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	60	$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	T_J	150	$^{\circ}\text{C}$
Storage Temperature 储藏温度	T_{stg}	$-55\text{to}+150^{\circ}\text{C}$	$^{\circ}\text{C}$

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Maximum 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.48	V	$I_F=10\text{A}$
Reverse Current 反向电流	$I_R(25^{\circ}\text{C})$ (125°C)	0.15 50	mA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D	570	pF	$V_R=4\text{V}$, $f=1\text{MHz}$



■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

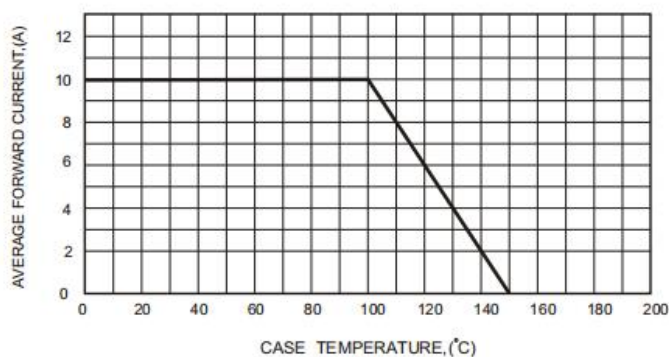


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

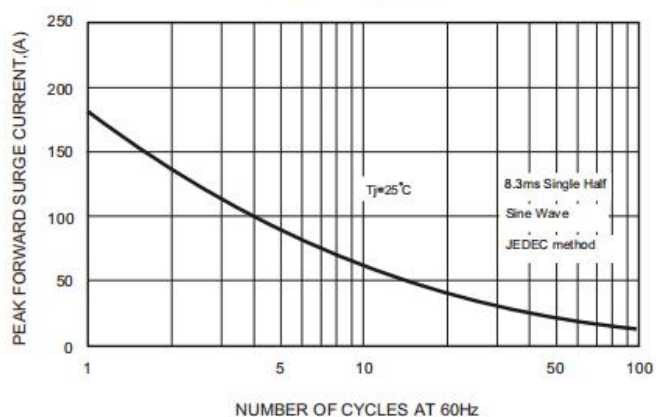


FIG.4-TYPICAL JUNCTION CAPACITANCE

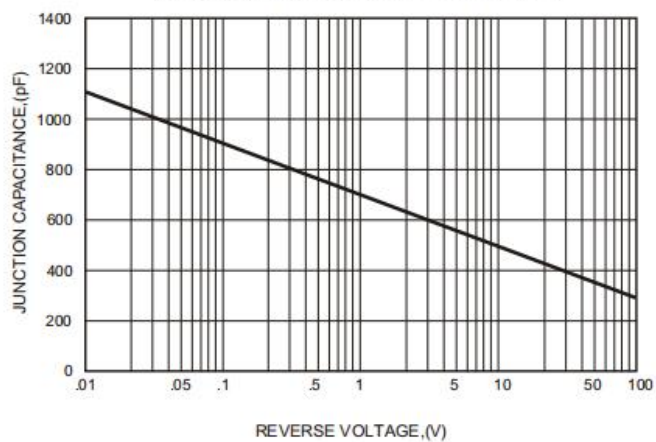


FIG.2-TYPICAL FORWARD CHARACTERISTICS

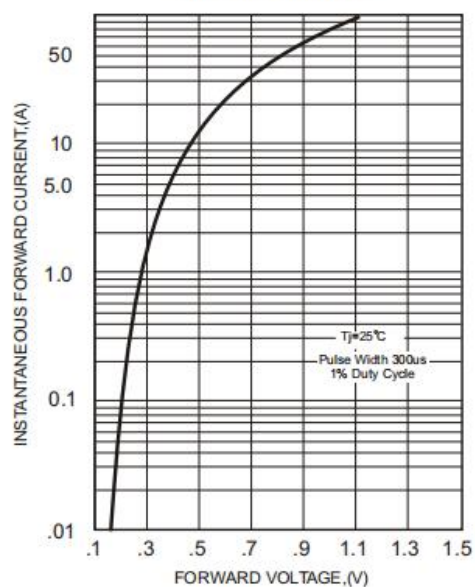
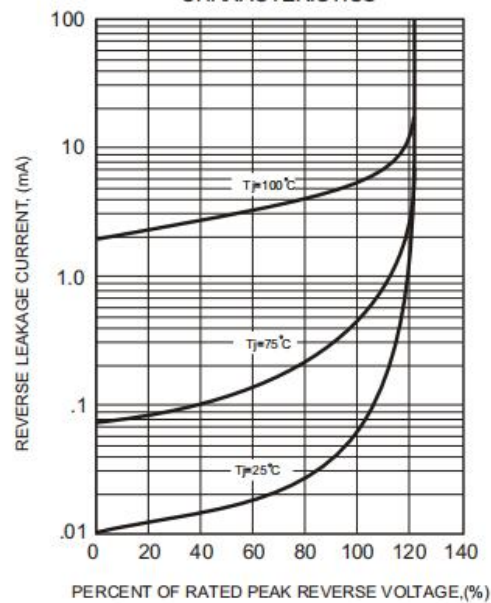
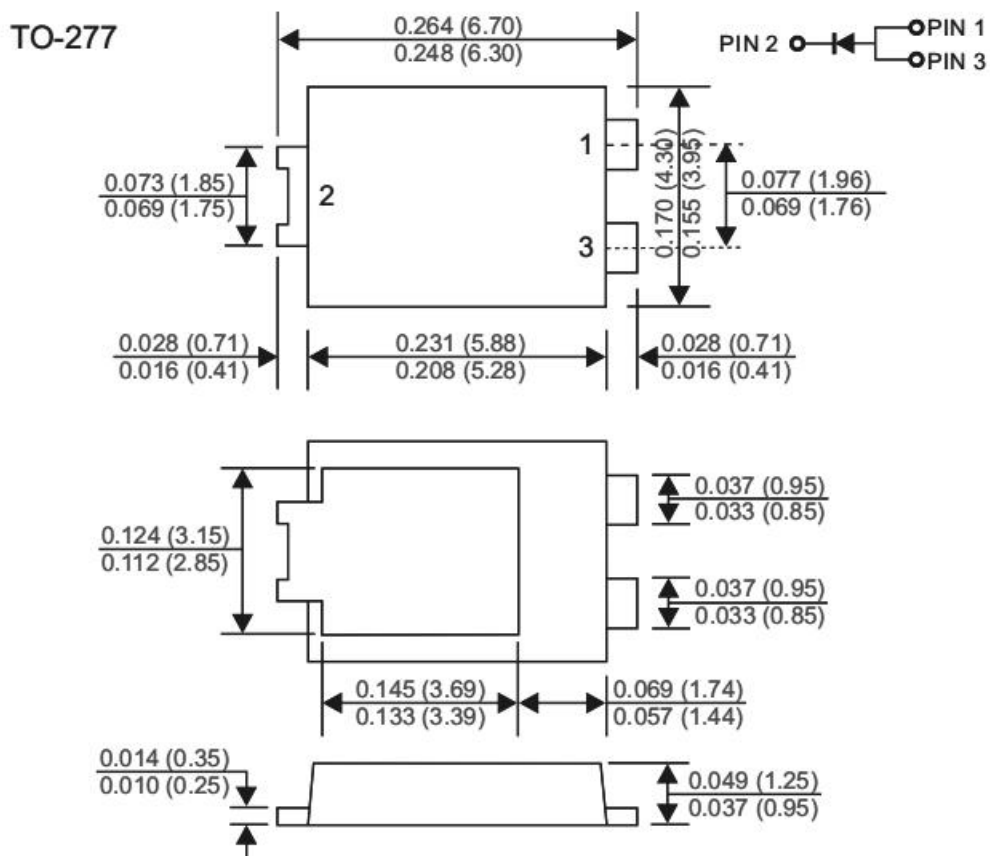


FIG.5 - TYPICAL REVERSE CHARACTERISTICS



■Dimension 外形封装尺寸



Dimensions in inches and (millimeters)